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# 2SB740

Silicon PNP Epitaxial

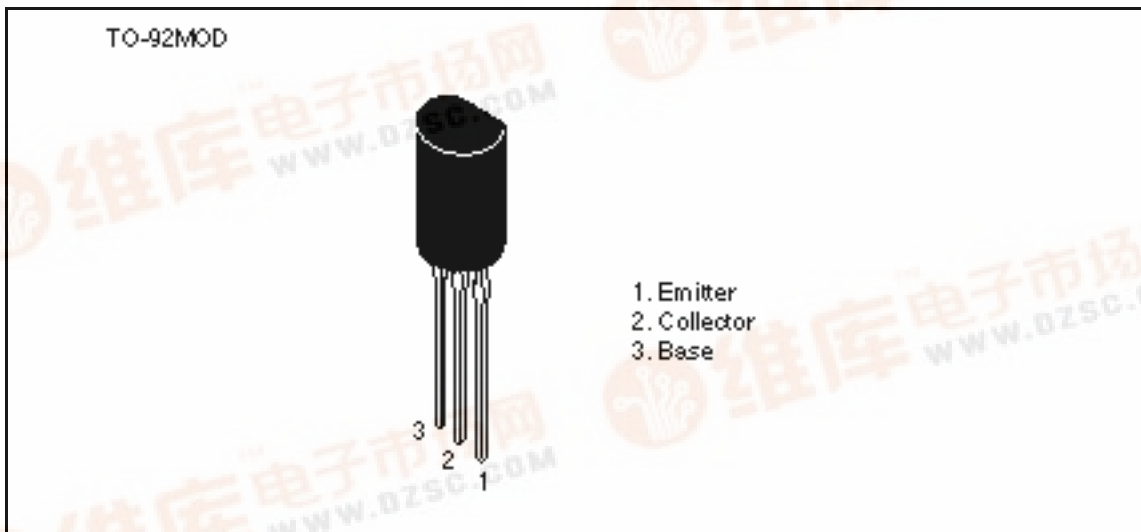
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## Application

- Low frequency power amplifier
- Complementary pair with 2SD789

## Outline



## 2SB740

### Absolute Maximum Ratings (Ta = 25°C)

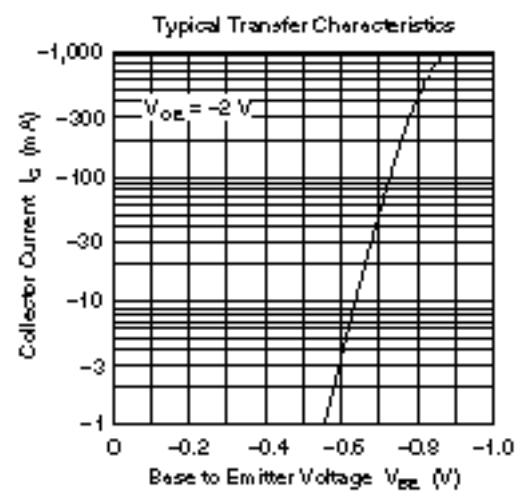
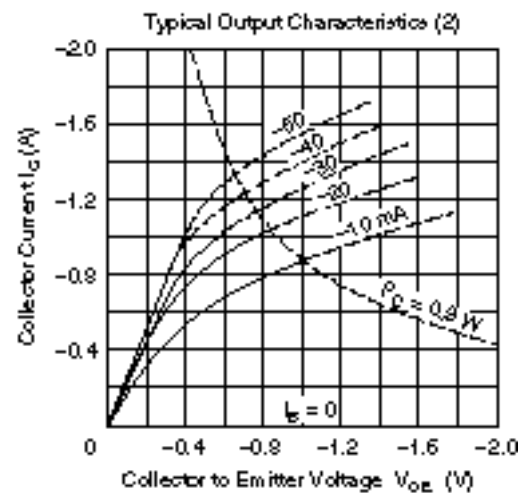
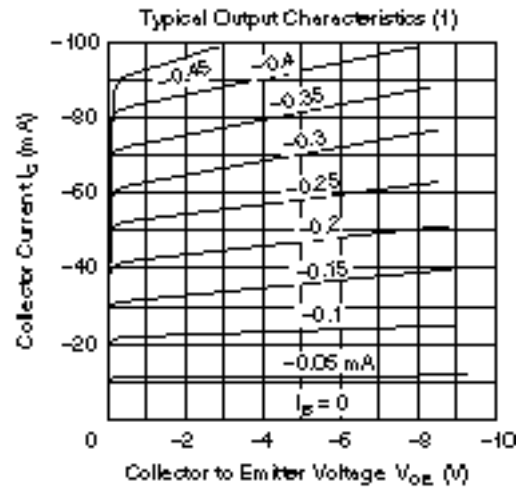
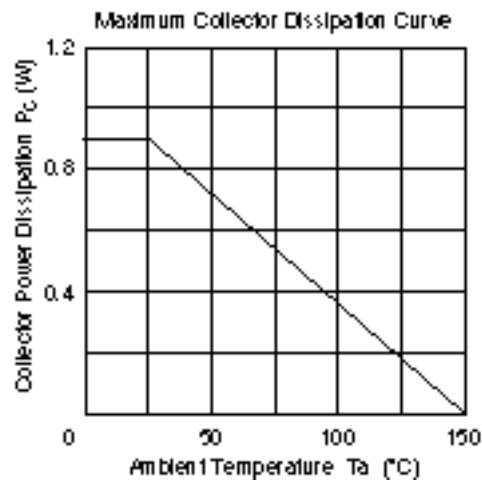
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	-70	V
Collector to emitter voltage	$V_{CEO}$	-50	V
Emitter to base voltage	$V_{EBO}$	-6	V
Collector current	$I_C$	-1	A
Collector power dissipation	$P_C$	0.9	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

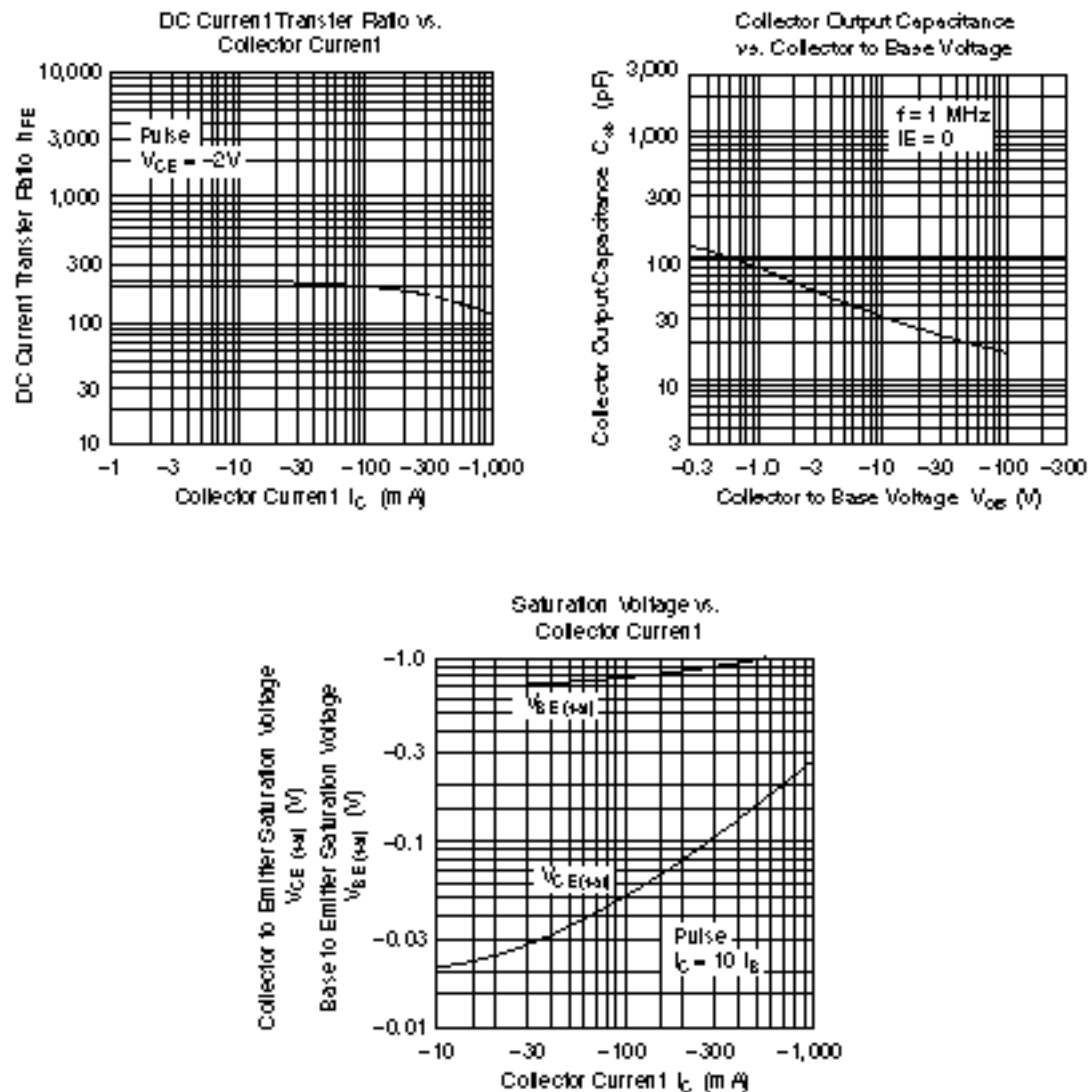
### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-70	—	—	V	$I_C = -10 \mu A$ , $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-50	—	—	V	$I_C = -1 \text{ mA}$ , $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	—	—	V	$I_E = -10 \mu A$ , $I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	-1	$\mu A$	$V_{CB} = -55 \text{ V}$ , $I_E = 0$
Emitter cutoff current	$I_{EBO}$	—	—	-0.2	$\mu A$	$V_{EB} = -6 \text{ V}$ , $I_C = 0$
DC current transfer ratio	$h_{FE}^{*1}$	100	—	320		$V_{CE} = -2 \text{ V}$ , $I_C = -0.1 \text{ A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.6	V	$I_C = -1 \text{ A}$ , $I_B = -0.1 \text{ A}$
Gain bandwidth product	$f_T$	—	150	—	MHz	$V_{CE} = -2 \text{ V}$ , $I_C = -10 \text{ mA}$
Collector output capacitance	$C_{ob}$	—	35	—	pF	$V_{CB} = -10 \text{ V}$ , $I_E = 0$ , $f = 1 \text{ MHz}$

Note: 1. The 2SB740 is grouped by  $h_{FE}$  as follows.

B	C
100 to 200	160 to 320





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